

1.Scope

The present specifications shall apply to an SJPZ-N33.

2.Outline

Type	Silicon Diode
Structure	Resin Molded
Applications	Over Voltage Absorption

3.Flammability

UL94V-0 (Equivalent)

4. Absolute maximum ratings

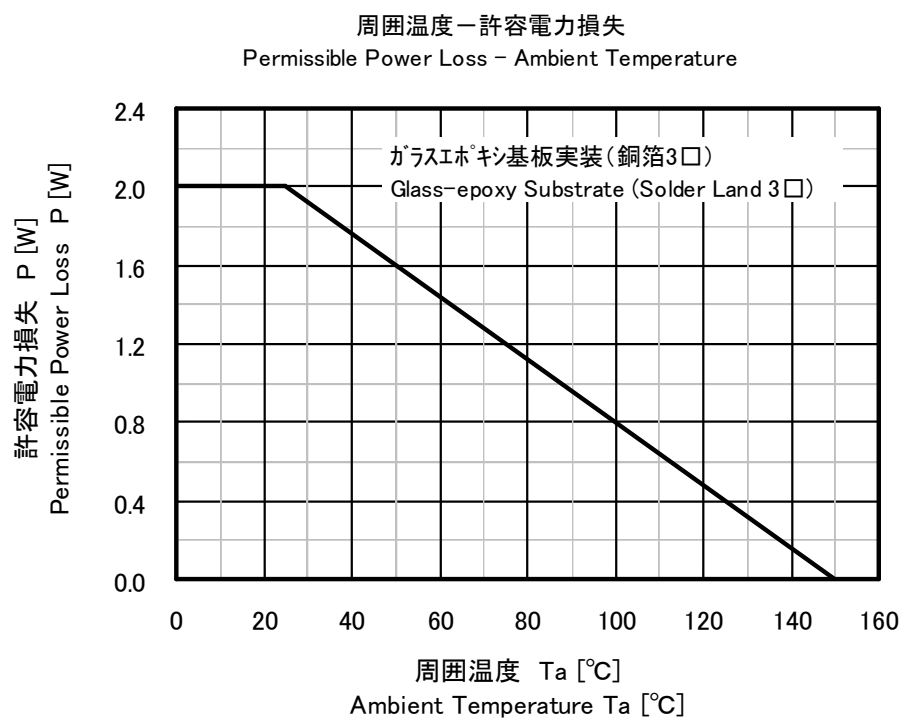
No.	Item	Symbol	Unit	Rating	Conditions
1	Permissible Power loss	P	W	2	Refer to Derating of 6
2	Transient Peak Reverse Power	P_{RSM}	W	500	Single Square Wave
3	Junction Temperature	T_j	°C	-55~+150	—
4	Storage Temperature	T_{stg}	°C	-55~+150	—

5. Electrical characteristics($T_a=25$, unless otherwise specified)

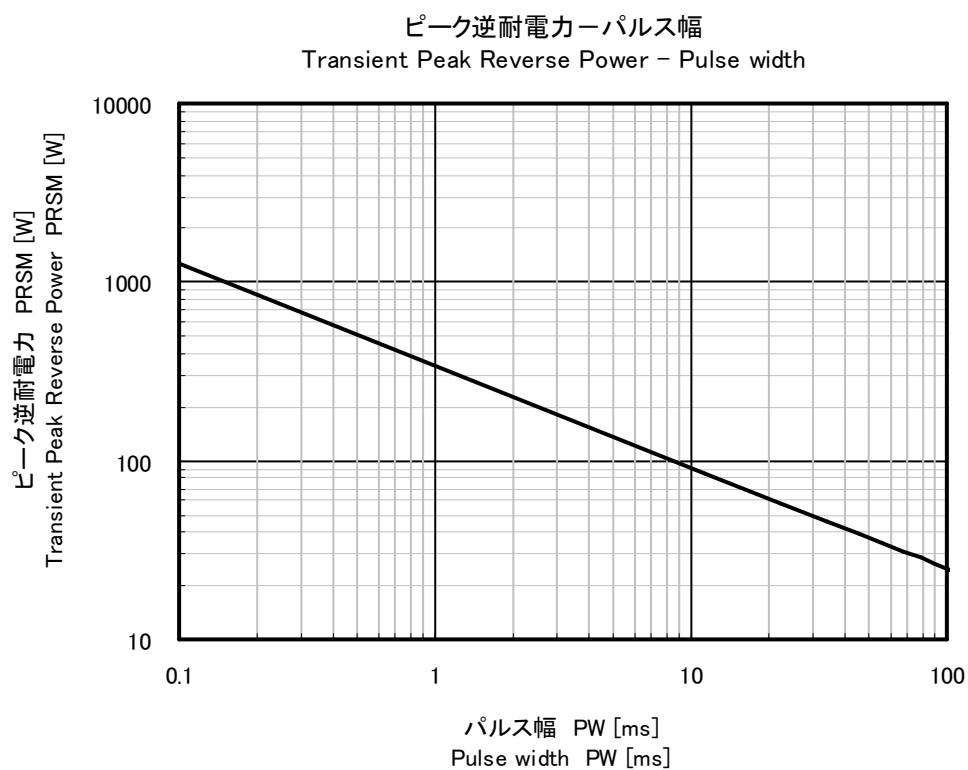
No.	Item	Symbol	Unit	Value	Conditions
1	Forward Voltage Drop	V_F	V	1.2 max.	$I_F=2A$
2	Reverse Breakdown Voltage	V_Z	V	31.0 ~ 35.0	$I_Z=1mA$
3	Reverse Leakage Current	I_R	uA	1 max.	$V_R=25V$
4	Temperature Coefficient Breakdown Voltage	γ_z	mV/°C	29 typ.	$I_Z=1mA$
5	Equivalent Resistance of Breakdown Region	R_z	Ω	5 typ.	$I_z=10mA \sim 20mA$

6. Derating

Permissible Power Loss

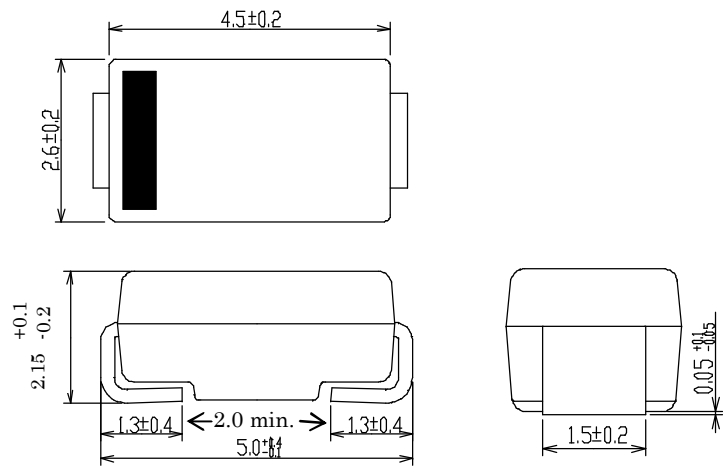


7. Transient Peak Reverse Power Rating



8. Package information

8-1 Package type, physical dimensions

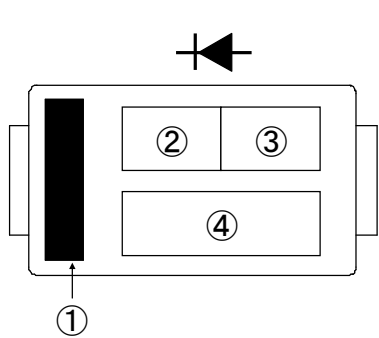


Dimensions in mm

8-2 Appearance

The body shall be clean and shall not bear any stain, rust or flaw.

8-3 Marking



- 1 Polarity marking (Cathode band)
- 2 Type number
SJPZ-N as abbreviated of ZN.
- 3 Vz Class number
33V as abbreviated of 33.
- 4 Lot number
Example) 9615
9: Last number of Year
6: Month from 1 to 9 for Jan. to Sep. O for Oct. , N for Nov. , D for Dec.
15: Day.

